

# **NPN Darlington Transistor**

This device is designed for applications requiring extremely high current gain at collector currents to 1.0 A. Sourced from Process 05.

#### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CES</sub>	Collector-Emitter Voltage	30	V
V <sub>CBO</sub>	Collector-Base Voltage	30	V
V <sub>EBO</sub>	Emitter-Base Voltage	10	V
I <sub>C</sub>	Collector Current - Continuous	1.2	А
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

# Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах			Units
		MPSA14	*MMBTA14	**PZTA14	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	1,000 8.0	mW mW/∘C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3			°C/W
$R_{ ext{ hetaJA}}$	Thermal Resistance, Junction to Ambient	200	357	125	°C/W

\*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

\*\* Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm<sup>2</sup>.

# NPN Darlington Transistor (continued)

Electrical Characteristics TA = 25°C unless otherwise noted					
Symbol	Parameter Test Conditions Min Max Un				Units
OFF CHARACTERISTICS					
V <sub>(BR)CES</sub>	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 100 \ \mu A, \ I_{\rm B} = 0$	30		V
I <sub>CBO</sub>	Collector-Cutoff Current $V_{CB} = 30 \text{ V}, I_E = 0$ 100		nA		
I <sub>EBO</sub>	Emitter-Cutoff Current $V_{EB} = 10 \text{ V}, I_C = 0$			100	nA

## **ON CHARACTERISTICS\***

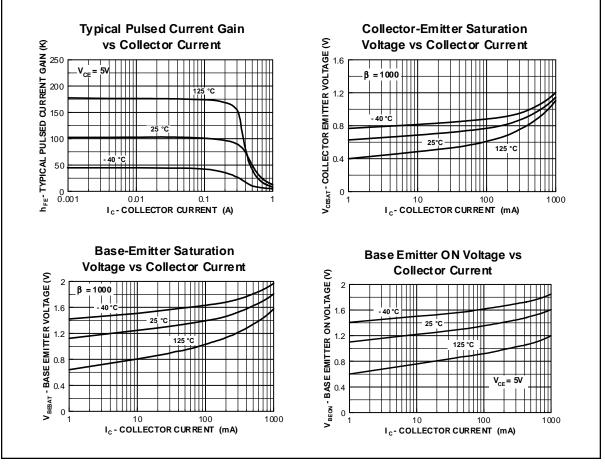
h <sub>FE</sub>	DC Current Gain	$I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_{C} = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$	10,000 20,000		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_{\rm C} = 100 \text{ mA}, I_{\rm B} = 0.1 \text{ mA}$		1.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	$I_{C} = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$		2.0	V

# SMALL SIGNAL CHARACTERISTICS

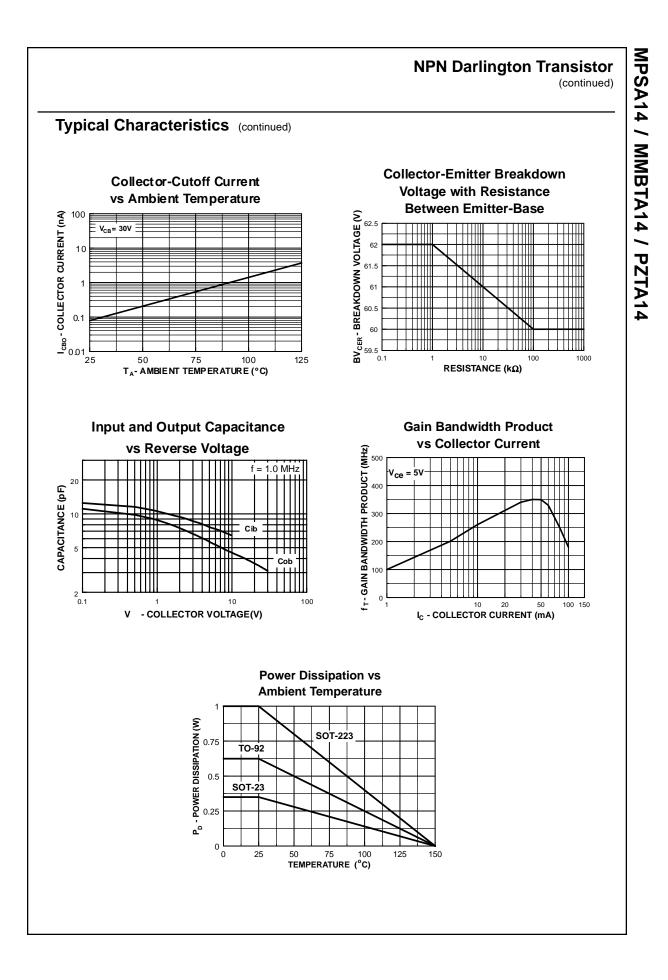
f⊤	Current Gain - Bandwidth Product	$I_{C} = 10 \text{ mA}, V_{CE} = 5 \text{ V},$ f = 100 MHz	125		MHz
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\*Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%

# **Typical Characteristics**



MPSA14 / MMBTA14 / PZTA14





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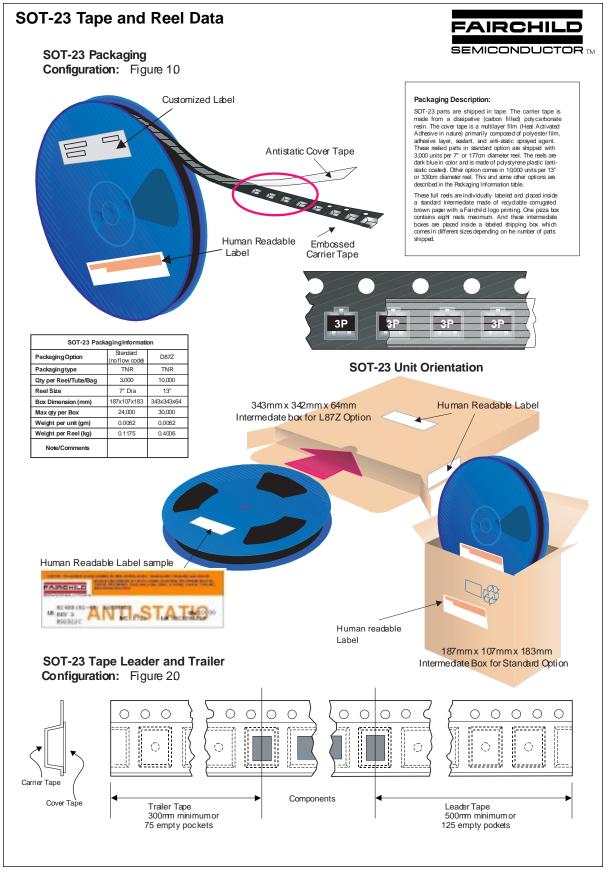
March 2001, Rev. B1





July 1999, Rev. A



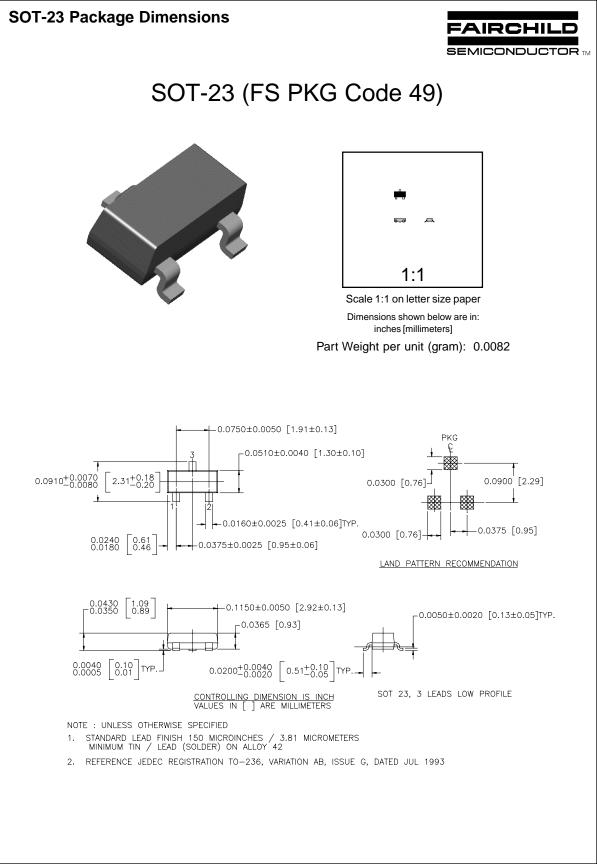


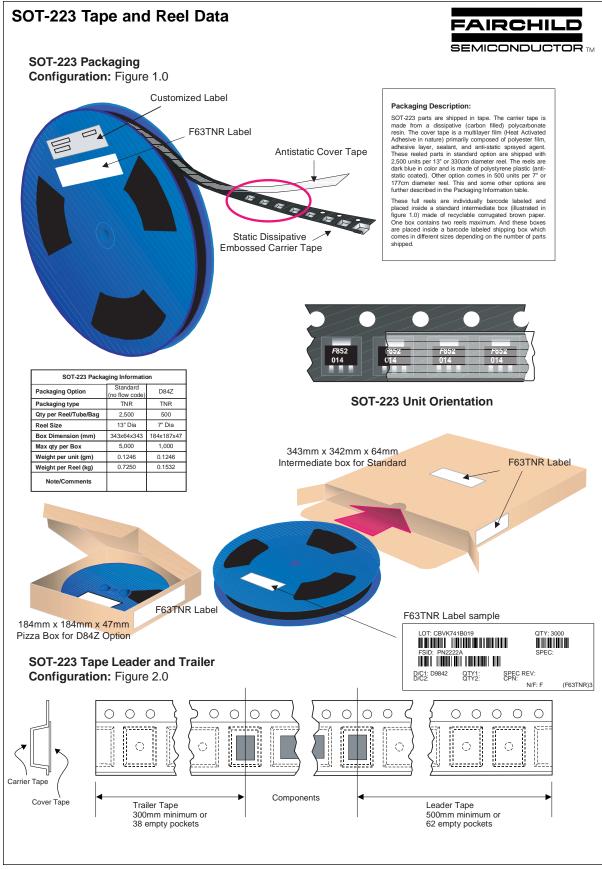
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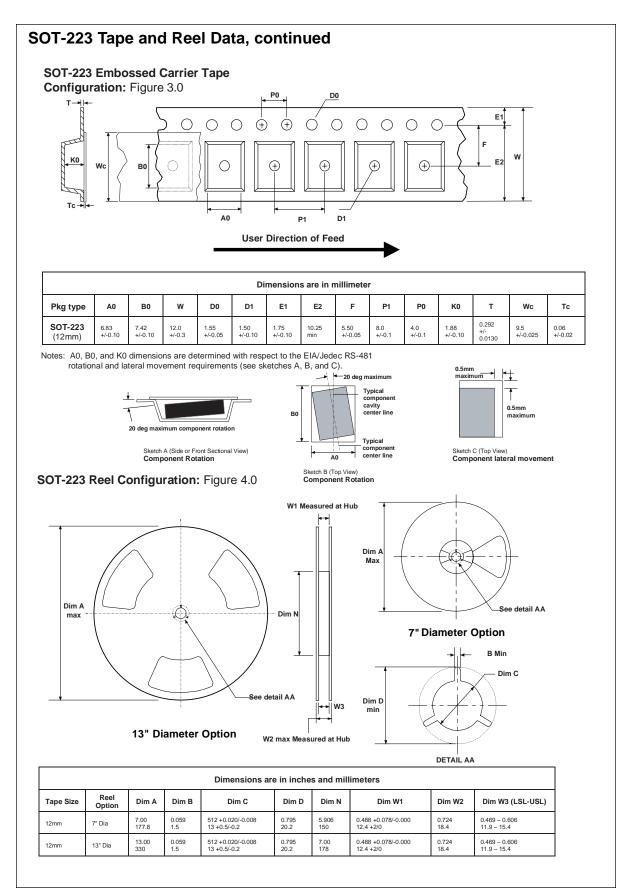
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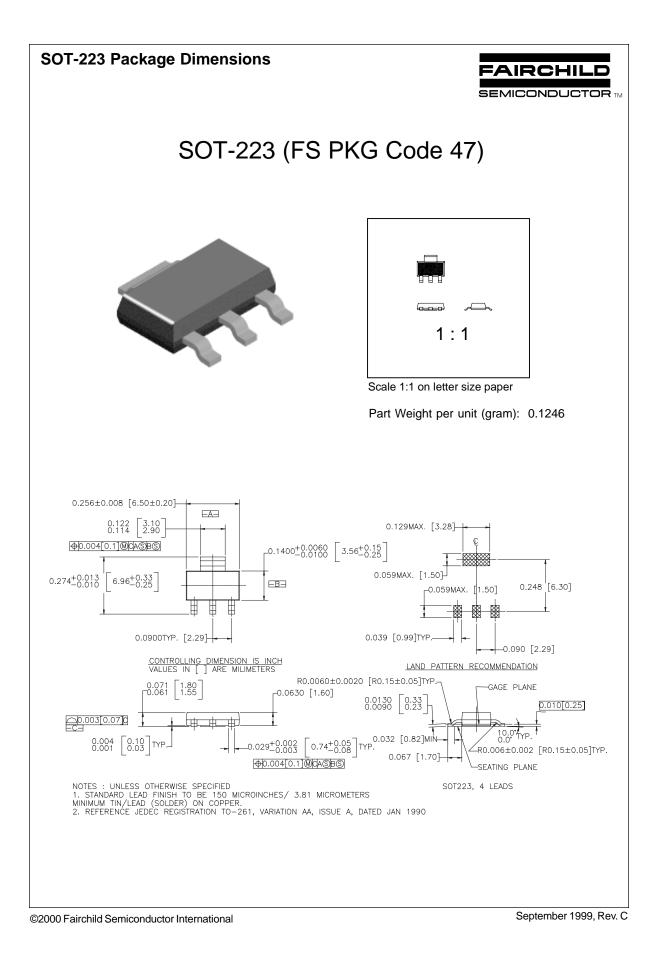




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